

BF992

Silicon N-channel dual gate MOS-FET

Rev. 04 — 21 November 2007

Product data sheet

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BF992

APPLICATIONS

- VHF applications such as VHF television tuners and FM tuners with 12 V supply voltage. The device is also suitable for use in professional communications equipment.

DESCRIPTION

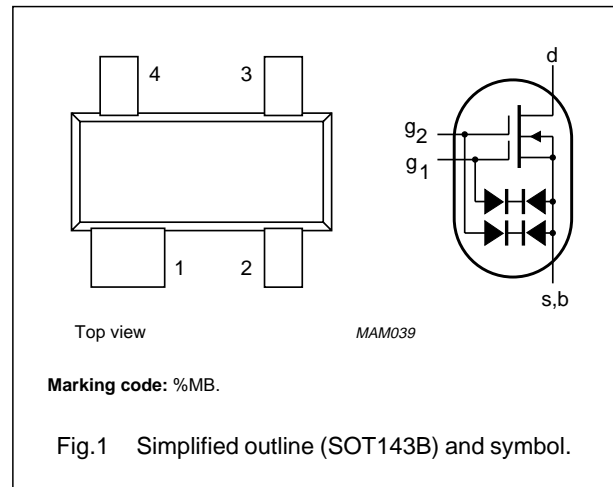
Depletion type field-effect transistor in a plastic micro-miniature SOT143B package with source and substrate interconnected.

The transistor is protected against excessive input voltage surges by integrated back-to-back diodes between gates and source.

CAUTION
The device is supplied in an antistatic package. The gate-source input must be protected against static discharge during transport or handling.

PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g_2	gate 2
4	g_1	gate 1



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage (DC)		–	20	V
I_D	drain current (DC)		–	40	mA
P_{tot}	total power dissipation	$T_{amb} = 60\text{ }^\circ\text{C}$	–	200	mW
$ Y_{fs} $	forward transfer admittance	$f = 1\text{ kHz}; I_D = 15\text{ mA}; V_{DS} = 10\text{ V}; V_{G2-S} = 4\text{ V}$	25	–	mS
C_{ig1-s}	input capacitance at gate 1	$f = 1\text{ MHz}; I_D = 15\text{ mA}; V_{DS} = 10\text{ V}; V_{G2-S} = 4\text{ V}$	4	–	pF
C_{rs}	reverse transfer capacitance	$f = 1\text{ MHz}; I_D = 15\text{ mA}; V_{DS} = 10\text{ V}; V_{G2-S} = 4\text{ V}$	30	–	fF
F	noise figure	$G_S = 2\text{ mS}; I_D = 15\text{ mA}; V_{DS} = 10\text{ V}; V_{G2-S} = 4\text{ V}; f = 200\text{ MHz}$	1.2	–	dB
T_j	operating junction temperature		–	150	$^\circ\text{C}$

Silicon N-channel dual gate MOS-FET

BF992

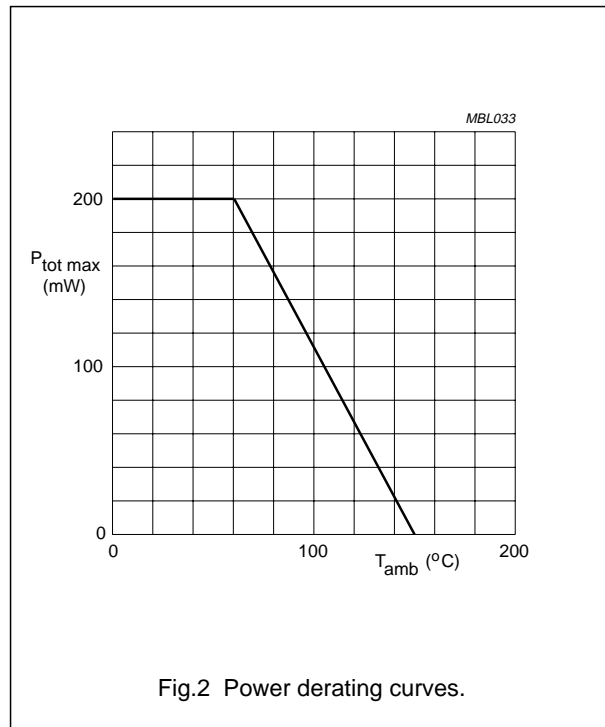
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	20	V
I_D	drain current		–	40	mA
I_{G1}	gate 1 current		–	±10	mA
I_{G2}	gate 2 current		–	±10	mA
P_{tot}	total power dissipation	$T_{amb} \leq 60\text{ °C}$; see Fig.2; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	150	°C

Note

1. Device mounted on a ceramic substrate, 8 mm × 10 mm × 0.7 mm.



Silicon N-channel dual gate MOS-FET

BF992

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient in free air	note 1	460	K/W

Note

1. Device mounted on a ceramic substrate, 8 mm × 10 mm × 0.7 mm.

STATIC CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$\pm V_{(BR)G1-SS}$	gate 1-source breakdown voltage	$V_{G2-S} = V_{DS} = 0$; $I_{G1-SS} = \pm 10\text{ mA}$	8	20	V
$\pm V_{(BR)G2-SS}$	gate 2-source breakdown voltage	$V_{G1-S} = V_{DS} = 0$; $I_{G2-SS} = \pm 10\text{ mA}$	8	20	V
$-V_{(P)G1-S}$	gate 1-source cut-off voltage	$V_{G2-S} = 4\text{ V}$; $V_{DS} = 10\text{ V}$; $I_D = 20\text{ }\mu\text{A}$	0.2	1.3	V
$-V_{(P)G2-S}$	gate 2-source cut-off voltage	$V_{G1-S} = 0$; $V_{DS} = 10\text{ V}$; $I_D = 20\text{ }\mu\text{A}$	0.2	1.1	V
$\pm I_{G1-SS}$	gate 1 cut-off current	$V_{G2-S} = V_{DS} = 0$; $V_{G1-S} = \pm 7\text{ V}$	–	25	nA
$\pm I_{G2-SS}$	gate 2 cut-off current	$V_{G1-S} = V_{DS} = 0$; $V_{G2-S} = \pm 7\text{ V}$	–	25	nA

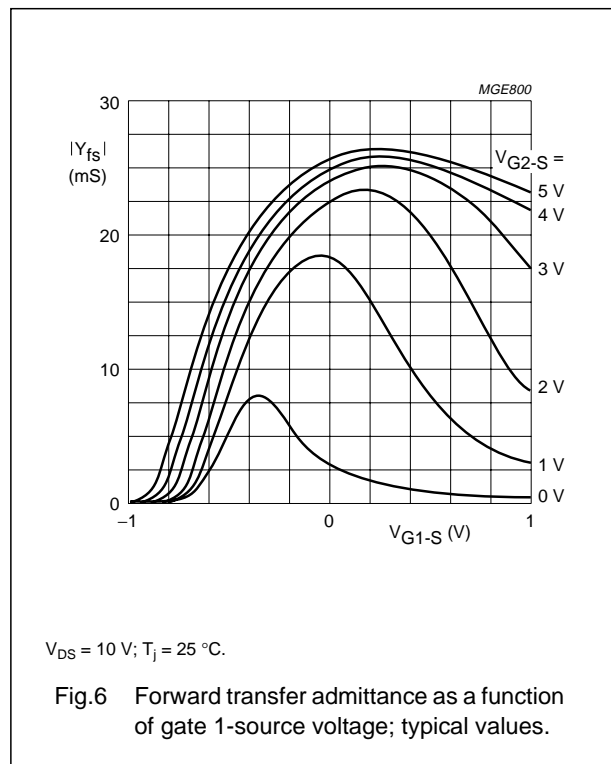
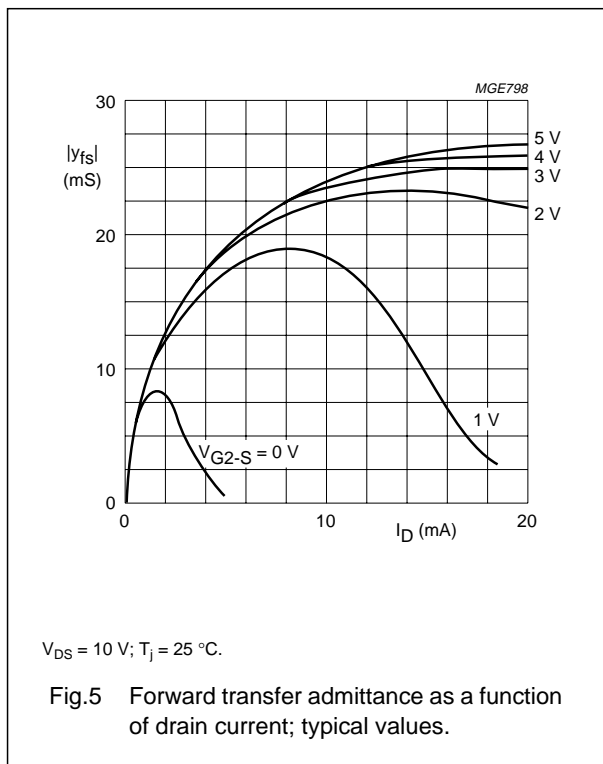
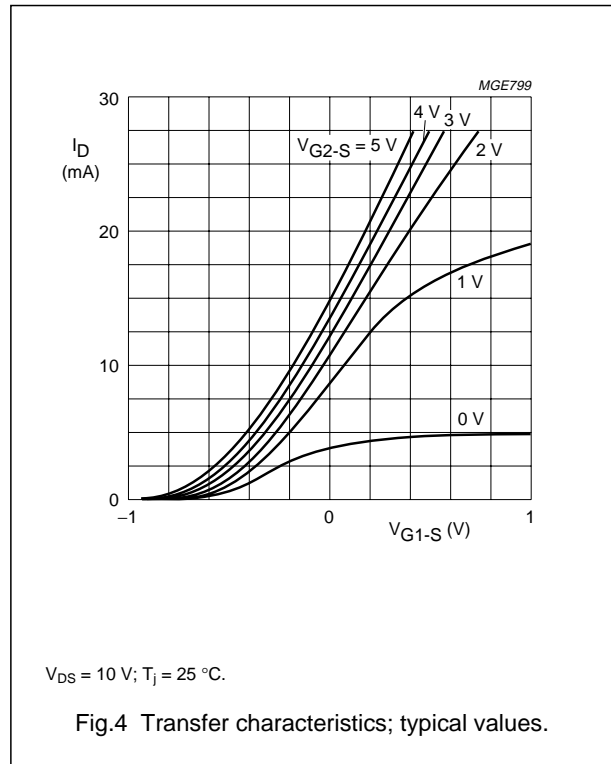
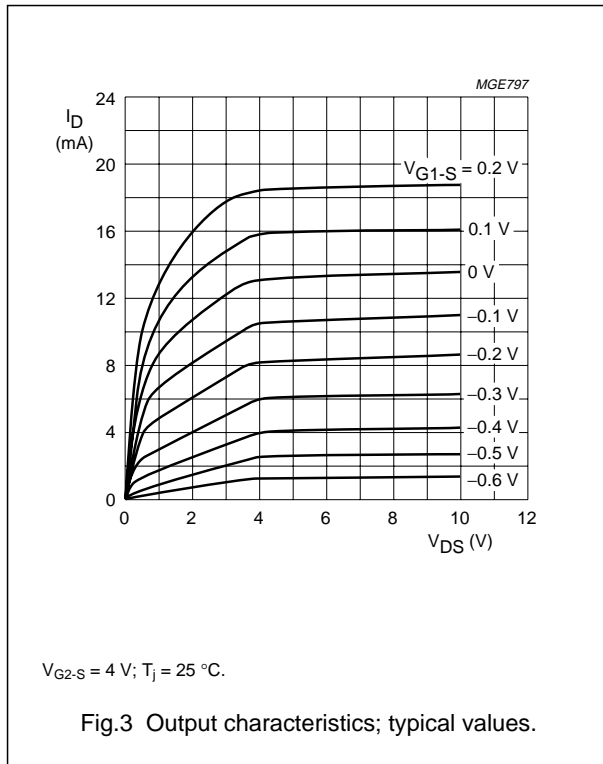
DYNAMIC CHARACTERISTICS

Common source; $T_{amb} = 25\text{ °C}$; $V_{DS} = 10\text{ V}$; $V_{G2-S} = 4\text{ V}$; $I_D = 15\text{ mA}$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$ y_{fs} $	forward transfer admittance		20	25	–	mS
C_{ig1-s}	input capacitance at gate 1	$f = 1\text{ MHz}$	–	4	–	pF
C_{ig2-s}	input capacitance at gate 2	$f = 1\text{ MHz}$	–	1.7	–	pF
C_{os}	output capacitance	$f = 1\text{ MHz}$	–	2	–	pF
C_{rs}	reverse transfer capacitance	$f = 1\text{ MHz}$	–	30	40	fF
F	noise figure	$f = 200\text{ MHz}$; $G_S = 2\text{ mS}$	–	1.2	–	dB

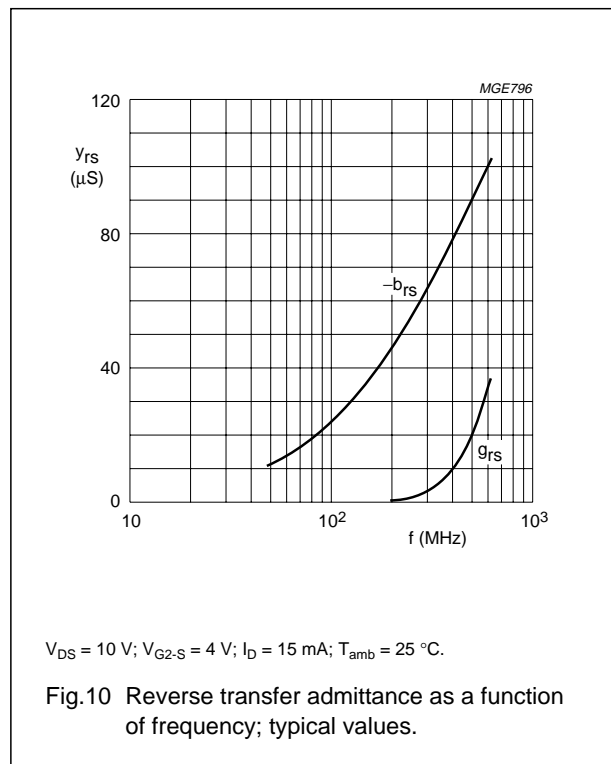
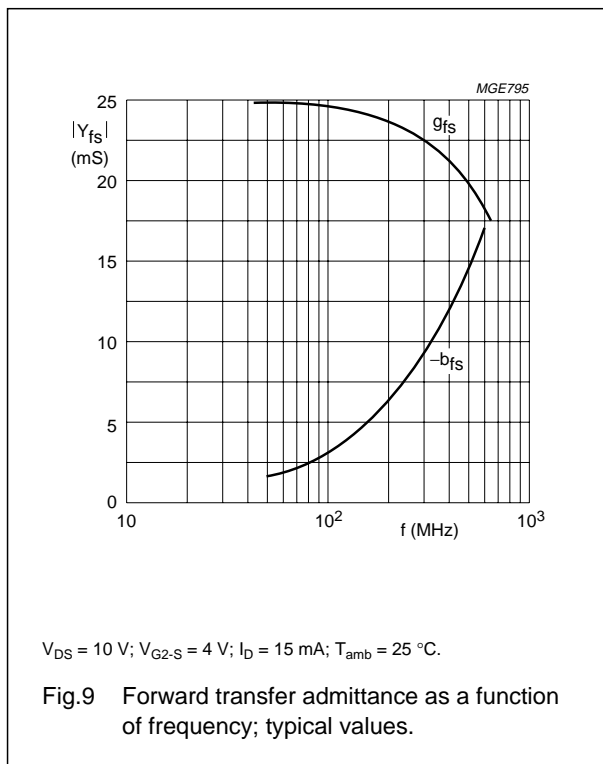
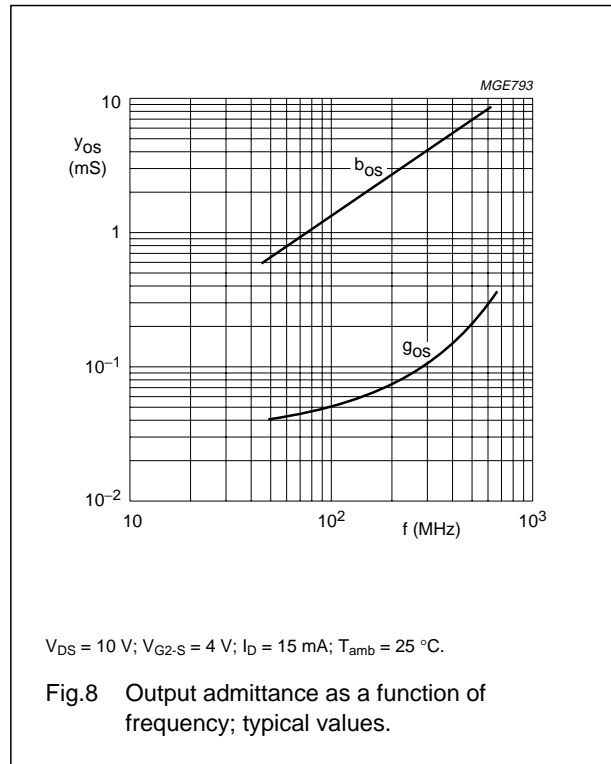
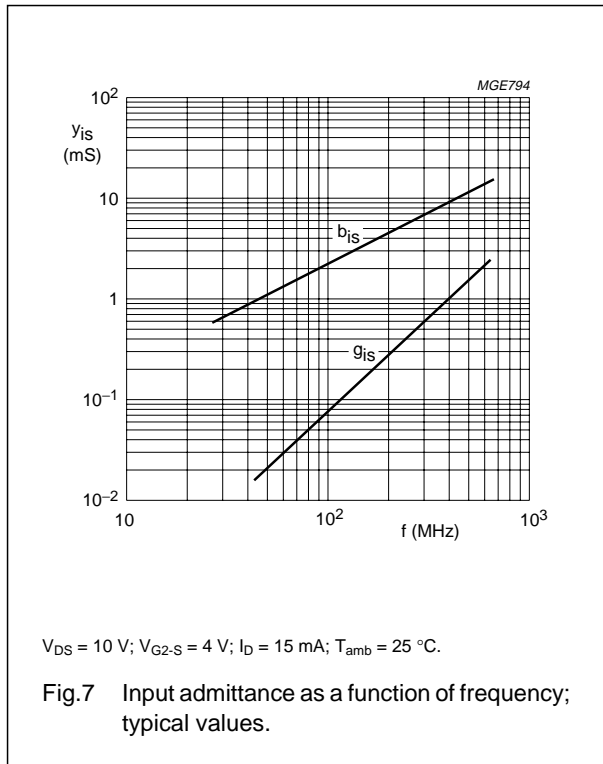
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BF992



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BF992



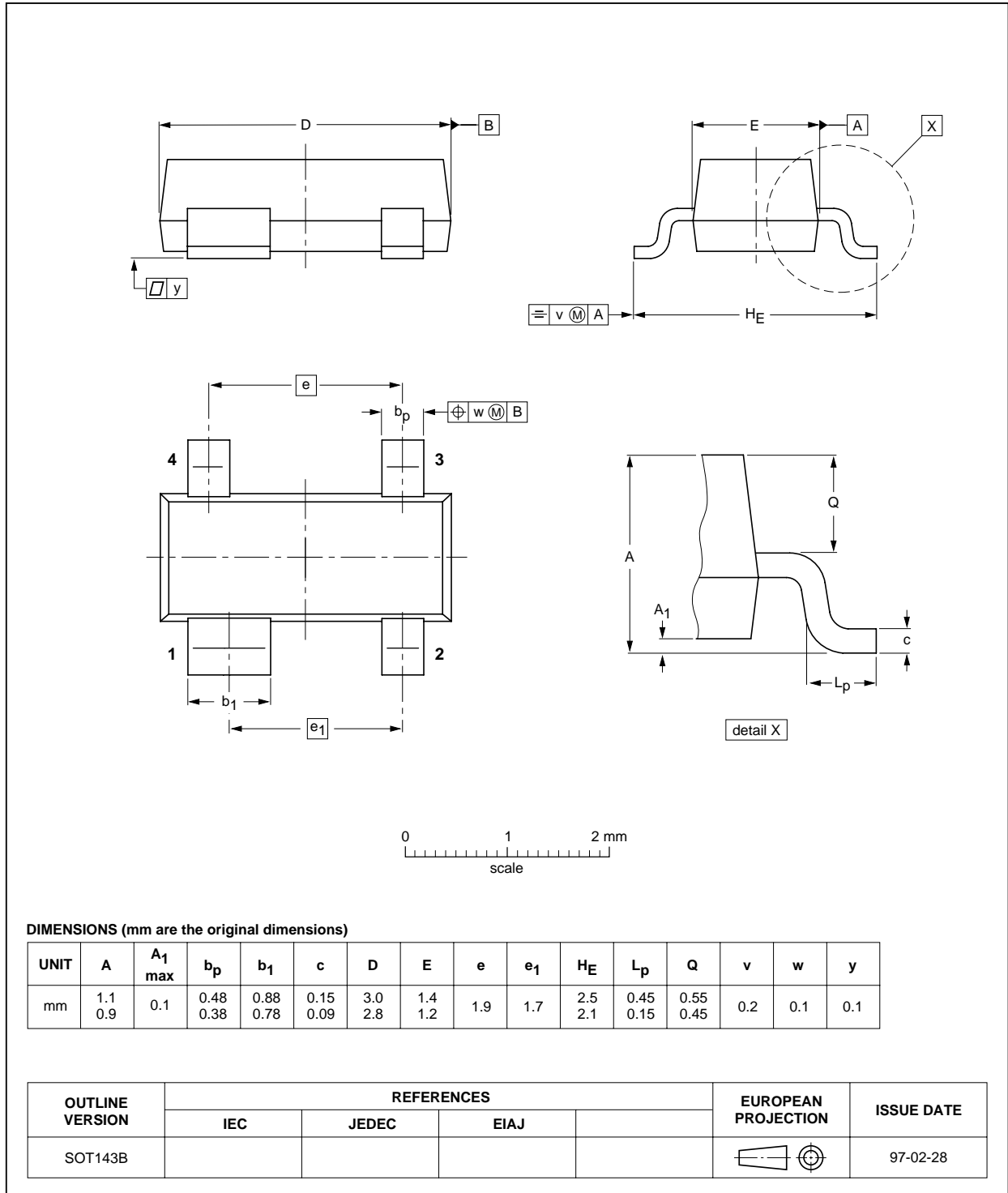
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BF992

PACKAGE OUTLINE

Plastic surface mounted package; 4 leads

SOT143B



Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BF992_N_4	20071121	Product data sheet	-	BF992_3
Modifications:	• Fig. 1 on page 2; Figure note changed			
BF992_3 (9397 750 06013)	19990811	Product specification	-	BF992_2
BF992_2	19960730	Product specification	-	BF992_SF_1
BF992_SF_1	-	-	-	-



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Document identifier: BF992_N_4